Silicon PNP Power Transistors 2SB794 2SB795

DESCRIPTION

·With TO-126 package
·DARLINGTON
·High DC current gain
·Low collector saturation voltage
·Complement to type 2SD985 2SD986

APPLICATIONS

·For use in operating from IC without predriver ,such as hammer driver

PINNING(See Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

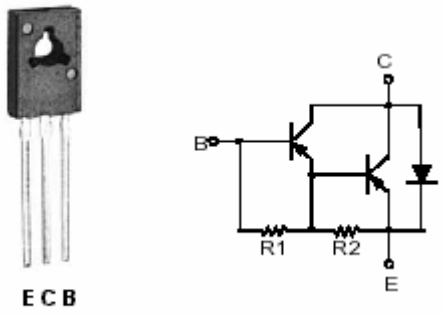

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SB794	Open emitter	-60	V
		2SB795		-80	
V_{CEO}	Collector-emitter voltage	2SB794	Open base	-60	V
		2SB795		-80	
V_{EBO}	Emitter-base voltage		Open collector	-8	V
I_C	Collector current (DC)			-1.5	A
I_{CM}	Collector current-peak			-3.0	A
P_D	Total power dissipation		T_a=25□	1.0	W
			T_C=25□	10	
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB794	I_C=-10mA ;I_B=0	-60			V
		2SB795		-80			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-1A ;I_B=-1mA			-1.5	V
V_{BEsat}	Base-emitter saturation voltage		I_C=-1A ;I_B=-1mA			-2.0	V
I_{CBO}	Collector cut-off current	2SB794	V_{CB}=-60V; I_E=0			-1.0	μA
		2SB795	V_{CB}=-80V; I_E=0				
I_{EBO}	Emitter cut-off current		V_{EB}=-5V; I_C=0			-2.0	mA
h_{FE-1}	DC current gain		I_C=-0.5A ; V_{CE}=-2V	1000			
h_{FE-2}	DC current gain		I_C=-1A ; V_{CE}=-2V	2000		30000	

Switching times

t_{on}	Turn-on time	I_C=-1.0A ; I_{B1}=-I_{B2}=-1.0mA V_{CC}=-50V;R_L=50Ω		0.5		μs
t_{stg}	Storage time			1.0		μs
t_f	Fall time			1.0		μs

◆ h_{FE-2} Classifications

M	L	K
2000-5000	4000-10000	8000-30000

PACKAGE OUTLINE

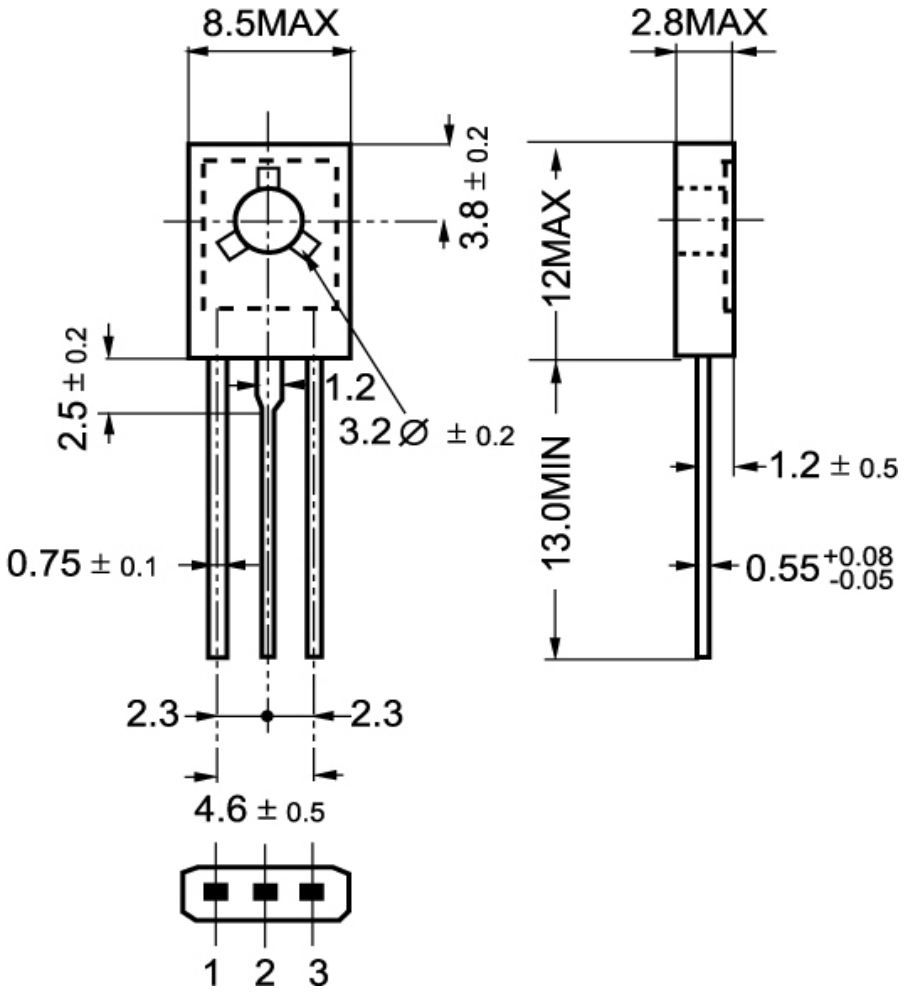

Fig.2 Outline dimensions